### DS75365 Quad TTL-to-MOS Driver

### **General Description**

The DS75365 is a quad monolithic integrated TTL-to-MOS driver and interface circuit that accepts standard TTL input signals and provides high-current and high-voltage output levels suitable for driving MOS circuits. It is used to drive address, control, and timing inputs for several types of MOS RAMs including the 1103.

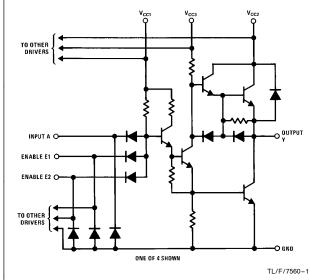
The DS75365 operates from the TTL 5V supply and the MOS V<sub>SS</sub> and V<sub>BB</sub> supplies in many applications. This device has been optimized for operation with V<sub>CC2</sub> supply voltage from 16V to 20V, and with nominal V<sub>CC3</sub> supply voltage from 3V to 4V higher than V<sub>CC2</sub>. However, it is designed so as to be usable over a much wider range of V<sub>CC2</sub> and V<sub>CC3</sub>. In some applications the V<sub>CC3</sub> power supply can be eliminated by connecting the V<sub>CC3</sub> to the V<sub>CC2</sub> pin.

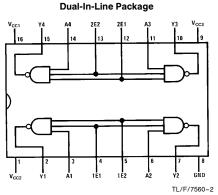
### **Features**

- Quad positive-logic NAND TTL-to-MOS driver
- Versatile interface circuit for use between TTL and high-current, high-voltage systems

- Capable of driving high-capacitance loads
- Compatible with many popular MOS RAMs
- Interchangeable with Intel 3207
- V<sub>CC2</sub> supply voltage variable over side range to 24V maximum
- V<sub>CC3</sub> supply voltage pin available
- V<sub>CC3</sub> pin can be connected to V<sub>CC2</sub> pin in some applications
- TTL compatible diode-clamped inputs
- Operates from standard bipolar and MOS supply voltages
- Two common enable inputs per gate-pair
- High-speed switching
- Transient overdrive minimizes power dissipation
- Low standby power dissipation

# Schematic and Connection Diagrams





Top View
Positive Logic: Y = A•E1•E2

Order Number DS75365N or DS75365WM See NS Package Number M16B or N16A

### **Absolute Maximum Ratings (Note 1)**

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Maximum Power Dissipation\* at 25°C

Cavity Package 1509 mW
Molded Package 1476 mW
SO Package 1488 mW
Lead Temperature (Soldering, 10 sec) 300°C

\* Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C, derate SO package 11.9 mW/°C above 25°C.

## **Operating Conditions**

	IVIIII	IVIAX	Ullits
Supply Voltage (V <sub>CC1</sub> )	4.75	5.25	V
Supply Voltage (V <sub>CC2</sub> )	4.75	24	V
Supply Voltage (V <sub>CC3</sub> )	$V_{CC2}$	28	V
Voltage Difference Between	0	10	V
Supply Voltages: V <sub>CC3</sub> -V <sub>CC2</sub>			
Operating Ambient Temperature	0	70	°C

Range (T<sub>A</sub>)

Symbol	Parameter	c	onditions	Min	Тур	Max	Units
V <sub>IH</sub>	High-Level Input Voltage			2			٧
V <sub>IL</sub>	Low-Level Input Voltage					0.8	٧
VI	Input Clamp Voltage	$I_{I} = -12 \text{ mA}$				-1.5	٧
V <sub>OH</sub>	High-Level Output Voltage	$V_{CC3} = V_{CC2} + 3V$	V <sub>CC2</sub> - 0.3	V <sub>CC2</sub> - 0.1		٧	
		$V_{CC3} = V_{CC2} + 3V, V_{IL} = 0.8V, I_{OH} = -10 \text{ mA}$		V <sub>CC2</sub> - 1.2	V <sub>CC2</sub> - 0.9		٧
		$V_{CC3} = V_{CC2}, V_{IL} = 0.8V, I_{OH} = -50 \mu A$		V <sub>CC2</sub> - 1	V <sub>CC2</sub> - 0.7		٧
		$V_{CC3} = V_{CC2}, V_{IL} =$	V <sub>CC2</sub> - 2.3	V <sub>CC2</sub> - 1.8		٧	
V <sub>OL</sub>	Low-Level Output Voltage				0.15	0.3	٧
		$V_{CC3} = 15V \text{ to } 28V,$	$V_{IH} = 2V$ , $I_{OL} = 40$ mA		0.25 0.		٧
V <sub>O</sub>	Output Clamp Voltage	$V_{I} = 0V, I_{OH} = 20 \text{ m}$			V <sub>CC2</sub> + 1.5	٧	
l <sub>l</sub>	Input Current at Maximum Input Voltage	V <sub>I</sub> = 5.5V			1	mA	
l <sub>IH</sub>	High-Level Input Current	V <sub>I</sub> = 2.4V	A Inputs			40	μΑ
			E1 and E2 Inputs			80	μΑ
I <sub>IL</sub>	Low-Level Input Current	V <sub>I</sub> = 0.4V	A Inputs		-1	-1.6	mA
		E1 and E2 Inputs	mA				
I <sub>CC1(H)</sub>	Supply Current from V <sub>CC1</sub> , All Outputs High	$V_{CC1} = 5.25V, V_{CC2} = 24V$ $V_{CC3} = 28V, All Inputs at 0V, No Load$			4	8	mA
I <sub>CC2(H)</sub>	Supply Current from V <sub>CC2</sub> ,				-2.2	+0.25	mA
	All Outputs High				-2.2	-3.2	mA
I <sub>CC3(H)</sub>	Supply Current from V <sub>CC3</sub> , All Outputs High				2.2	3.5	mA
I <sub>CC1(L)</sub>	Supply Current from V <sub>CC1</sub> , All Outputs Low	V <sub>CC1</sub> = 5.25V, V <sub>CC2</sub> = 24V V <sub>CC3</sub> = 28V, All Inputs at 5V, No Load			31	47	mA
I <sub>CC2(L)</sub>	Supply Current from V <sub>CC2</sub> , All Outputs Low					3	mA
I <sub>CC3(L)</sub>	Supply Current from V <sub>CC3</sub> , All Outputs Low				16	25	mA
I <sub>CC2(H)</sub>	Supply Current from V <sub>CC2</sub> , All Outputs High	$V_{CC1} = 5.25V, V_{CC2}$ $V_{CC3} = 24V, All Inpu$				0.25	mA
I <sub>CC3(H)</sub>	Supply Current from V <sub>CC3</sub> , All Outputs High					0.5	mA

Electrical Characteristics (Notes 2 and 3)

### Electrical Characteristics (Notes 2, 3) (Continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
I <sub>CC2(S)</sub>	Supply Current from V <sub>CC2</sub> , Stand-By Condition	$V_{CC1} = 0V$ , $V_{CC2} = 24V$ $V_{CC3} = 24V$ , All Inputs at 5V, No Load			0.25	mA
I <sub>CC3(S)</sub>	Supply Current from V <sub>CC3</sub> , Stand-By Condition				0.5	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0°C to +70°C range for the DS75365. All typical values are for  $T_A = 25$ °C and  $V_{CC1} = 5V$  and  $V_{CC2} = 20V$  and  $V_{CC3} = 24V$ .

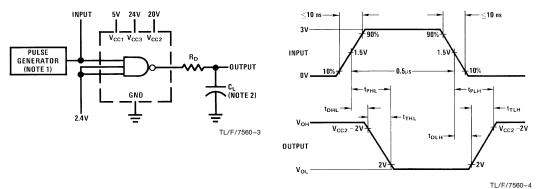
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: This rating applies between any two inputs of any one of the gates.

## Switching Characteristics $V_{CC1} = 5V$ , $V_{CC2} = 20V$ , $V_{CC3} = 24V$ , $T_A = 25^{\circ}C$

Symbol	Parameter	Conditions	Min	Тур	Max	Units
t <sub>DLH</sub>	Delay Time, Low-to-High Level Output	$C_L = 200  pF$		11	20	ns
t <sub>DHL</sub>	Delay Time, High-to-Low Level Output	$R_D = 24\Omega$		10	18	ns
t <sub>TLH</sub>	Transition Time, Low-to-High Level Output	(Figure 1)		20	33	ns
t <sub>THL</sub>	Transition Time, High-to-Low Level Output			20	33	ns
t <sub>PLH</sub>	Propagation Delay Time, Low-to-High Level Output		10	31	48	ns
t <sub>PHL</sub>	Propagation Delay Time, High-to-Low Level Output		10	30	46	ns

# **AC Test Circuit and Switching Time Waveforms**

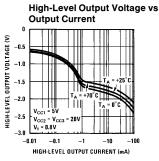


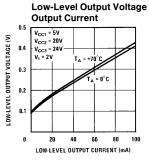
Note 1: The pulse generator has the following characteristics: PRR = 1 MHz,  $Z_{OUT} = 58 \Omega$ .

Note 2: C<sub>L</sub> includes probe and jig capacitance.

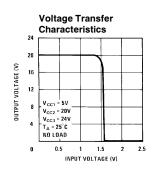
FIGURE 1. Switching Times, Each Driver

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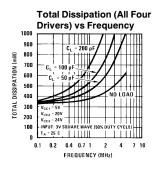




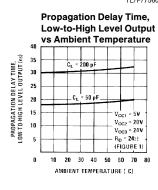


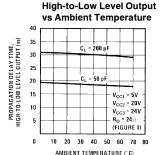
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HIGH-LEVEL OUTPUT CURRENT (mA)

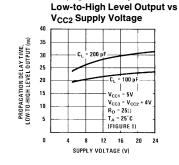


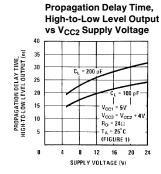
**Propagation Delay Time,** 

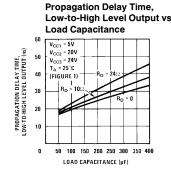


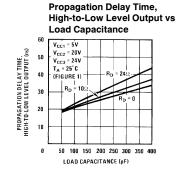


**Propagation Delay Time,** 









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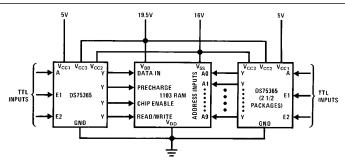
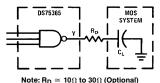


FIGURE 2. Interconnection of DS75365 Devices with 1103-Type Silicon-Gate MOS RAM

TL/F/7560-7

### **Typical Applications**

The fast switching speeds of this device may produce undesirable output transient overshoot because of load or wiring inductance. A small series damping resistor may be used to reduce or eliminate this output transient overshoot. The optimum value of the damping resistor depends on the specific load characteristics and switching speed. A typical value would be between  $10\Omega$  and  $30\Omega$  (Figure 3).



TI /F/7560-8

FIGURE 3. Use of Damping Resistor to Reduce or Eliminate Output Transient Overshoot in Certain DS75365 Applications

### **Thermal Information**

#### POWER DISSIPATION PRECAUTIONS

Significant power may be dissipated in the DS75365 driver when charging and discharging high-capacitance loads over a wide voltage range at high frequencies. The total dissipation curve shows the power dissipated in a typical DS75365 as a function of load capacitance and frequency. Average power dissipation by this driver can be broken into three components:

$$P_{T(AV)} = P_{DC(AV)} + P_{C(AV)} + P_{S(AV)}$$

where  $P_{DC(AV)}$  is the steady-state power dissipation with the output high or low,  $P_{C(AV)}$  is the power level during charging or discharging of the load capacitance, and  $P_{S(AV)}$  is the power dissipation during switching between the low and high levels. None of these include energy transferred to the load and all are averaged over a full cycle.

The power components per driver channel are:

$$\begin{split} P_{DC(AV)} &= \frac{P_L t_L + P_H t_H}{T} \\ P_{C(AV)} &\cong C \, V C^2 f \\ P_{S(AV)} &= \frac{P_{LH} t_{LH} + P_{HL} t_{HL}}{T} \end{split}$$

where the times are as defined in Figure 4.

 $P_L$ ,  $P_H$ ,  $P_{LH}$ , and  $P_{HL}$  are the respective instantaneous levels of power dissipation and C is load capacitance.

The DS75365 is so designed that  $P_S$  is a negligible portion of  $P_T$  in most applications. Except at very high frequencies,  $t_L + t_H \gg t_{LH} + t_{HL}$  so that  $P_S$  can be neglected. The total dissipation curve for no load demonstrates this point. The power dissipation contributions from all four channels are then added together to obtain total device power.

The following example illustrates this power calculation technique. Assume all four channels are operating identically with C = 100 pF, f = 2 MHz,  $V_{CC1}=5V,\,V_{CC2}=20V,\,V_{CC3}=24V$  and duty cycle = 60% outputs high (t<sub>H</sub>/T = 0.6). Also, assume  $V_{OH}=20V,\,V_{OL}=0.1V,\,P_S$  is negligible, and that the current from  $V_{CC2}$  is negligible when the output is low.

On a per-channel basis using data sheet values:

$$\begin{split} P_{DC(AV)} &= \left[ (5V) \left( \frac{4 \text{ mA}}{4} \right) + (20V) \left( \frac{-2.2 \text{ mA}}{4} \right) + (24V) \right. \\ &\left. \left( \frac{2.2 \text{ mA}}{4} \right) \right] (0.6) + \left[ (5V) \left( \frac{31 \text{ mA}}{4} \right) + (24V) \left( \frac{16 \text{ mA}}{4} \right) \right] (0.4) \end{split}$$

 $P_{DC(AV)} = 58 \text{ mW per channel}$ 

 $P_{C(AV)} \cong (100 \text{ pF}) (19.9\text{V})^2 (2 \text{ MHz})$ 

 $P_{C(AV)} \approx 79 \text{ mW per channel.}$ 

For the total device dissipation of the four channels:

 $P_{T(AV)} \cong 4 (58 + 79)$ 

 $P_{T(AV)} \simeq 548$  mW typical for total package.

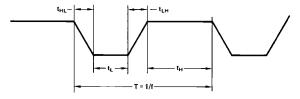
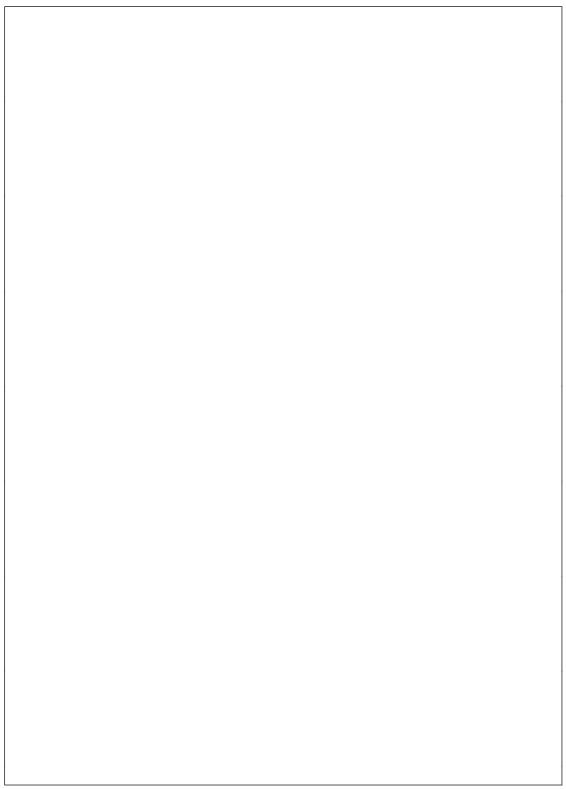
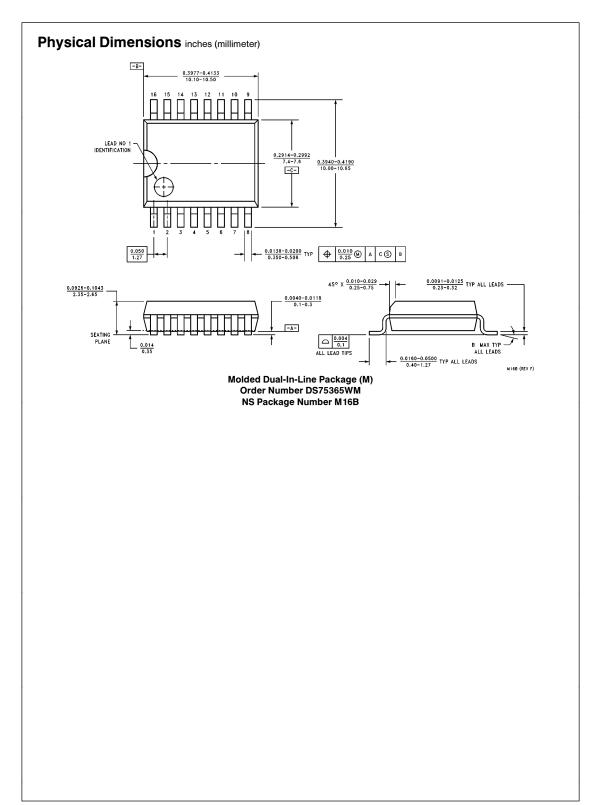


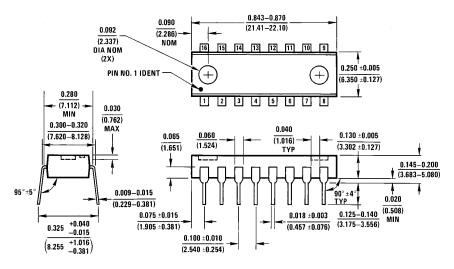
FIGURE 4. Output Voltage Waveform

TL/F/7560-9





### Physical Dimensions inches (millimeter) (Continued)



Molded Dual-In-Line Package (N) Order Number DS75365N NS Package Number N16A

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N16A (REV E)



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